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## INFORMATION DISCLOSURE STATEMENT

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## **US PATENT DOCUMENTS**

Examiner Initial		Document Number	Date	Name	Class	Sub- Class	Filing Date
/HQH/	AA	US-6,413,822 B2	07-02-2002	Williams et al.			

## **FOREIGN PATENT DOCUMENTS**

Examiner Initial		Document Number	Date	Country	Class	Sub- Class	Translation
/HQH/:	AB	2003-92386	03-28-2003	JAPAN			Abstract and translation
/HQH/	AC	EP 1 168 455 A2	01-02-2002	EUROPE			N/a

## OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

ΑD /HQH/

SAGGIO M ET AL: "MDMESH<sup>TM</sup>: INNOVATIVE TECHNOLOGY FOR HIGH VOLTAGE POWERMOSFETS" PROCEEDINGS OF THE INTERNATIONAL SYMPOSIUM ON

POWERSEMICONDUCTOR DEVICES AND ICS, NEW YORK, NY, US, 22 May 2000 (2000-05-

22), pages 65-68, XP000985371

Examiner:

/Hoang Quan Ho/

Date Considered:

02/02/2009

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.